

BCW70 PNP EPITAXIAL SILICON TRANSISTOR**GENERAL PURPOSE TRANSISTOR****ABSOLUTE MAXIMUM RATINGS (T_a = 25°C)**

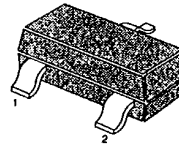
Characteristic	Symbol	Rating	Unit
Collector-Emitter Voltage	V _{CEO}	45	V
Emitter-Base Voltage	V _{EB0}	5	V
Collector Current	I _C	100	mA
Collector Dissipation	P _C	350	mW
Storage Temperature	T _{stg}	150	°C

• Refer to MMBT5086 for graphs

ELECTRICAL CHARACTERISTICS (T_a = 25°C)

Characteristic	Symbol	Test Condition	Min	Max	Unit
Collector-Emitter Breakdown Voltage	BV _{CEO}	I _C = 2.0mA, I _B = 0	45		V
Collector-Emitter Breakdown Voltage	BV _{CES}	I _C = 100μA, V _{EB} = 0	50		V
Emitter-Base Breakdown Voltage	BV _{EBO}	I _E = 10μA, I _C = 0	5		V
Collector Cutoff Current	I _{CBO}	V _{CB} = 20V, I _E = 0		100	nA
DC Current Gain	h _{FE}	V _{CE} = 5V, I _C = 2.0mA	215	500	
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C = 10mA, I _B = 0.5mA		0.3	V
Base-Emitter On Voltage	V _{BE(on)}	I _C = 2.0mA, V _{CE} = 5V	0.6	0.75	V
Output Capacitance	C _{ob}	V _{CB} = 10V, I _E = 0 f = 1.0MHz		7.0	pF
Noise Figure	NF	I _C = 0.2mA, V _{CE} = 5.0V R _S = 2.0KΩ, f = 1.0KHz		10	dB

SOT-23



1. Base 2. Emitter 3. Collector

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Marking

